

33. (Amended) The integrated circuit of claim 32 wherein the control stack of each MOS transistor comprises a gate stack including an oxide layer, polysilicon layer, silicide layer, another oxide layer, and a nitride layer.

35. (Amended) The integrated circuit of claim 34 wherein the electromagnetic radiation comprises collimated light.

-- 37. (New) The integrated circuit of claim 30 wherein an insulating spacer layer is disposed between the control stack and the contacts.

38. (New) An in-process substrate structure including a plurality of contact regions and a plurality of non-contact regions adjacent the contact regions on an upper surface of the substrate, the in-process substrate structure comprising:

a contact formed on each contact region, each contact having a top surface and two sidewall surfaces disposed between the top surface and the upper surface of the substrate, the top surface being heated to increase a vertical growth rate of the contact relative to a horizontal growth rate of the contact so that each sidewall remains substantially vertical and overlap of the contact into adjacent non contact regions due to lateral growth is limited.

39. (New) The substrate of claim 38 wherein the top surface is substantially parallel to the upper surface of the substrate.

40. (New) The substrate of claim 38 wherein the top surface is substantially horizontal.

41. (New) The substrate of claim 38 wherein the contact is heated by illuminating an upper surface of the contact with electromagnetic radiation.

42. (New) The substrate of claim 41 wherein the electromagnetic radiation comprises collimated light.

43. (New) The substrate of claim 42 wherein the collimated light comprises a scanning laser beam.

44. (New) The substrate of claim 42 wherein the collimated light is propagated substantially perpendicular to the top surface of the contact.

45. (New) The substrate of claim 38 wherein the non-contact regions adjacent to the contact region comprise isolation oxide regions.

46. (New) The substrate of claim 38 wherein the substrate comprises silicon.

47. (New) The substrate of claim 38 wherein the substrate comprises gallium arsenide.

48. (New) The substrate of claim 38 wherein the substrate comprises silicon germanium.

49. (New) The substrate of claim 38 wherein the contact comprises silicon.

50. (New) The substrate of claim 38 wherein the contact comprises gallium arsenide.

51. (New) The substrate of claim 38 wherein the contact comprises silicon germanium. --